

AMENDMENT TO THE CLAIMS:

Please cancel claim 1, and amend claims 3 and 4.

Claims 1 and 2 (Canceled)

3. (Currently amended) The microstrip line of claim 1, A microstrip line comprising:

a ground conductor layer;

a dielectric layer disposed on the ground conductor layer;

a linear conductor layer disposed on the dielectric layer to have a linear configuration,

the linear conductor layer having a wider portion in an upper part of a cross section thereof taken in a direction perpendicular to a direction in which the linear conductor layer extends and a narrower portion in a lower part of the cross section, the narrower portion being smaller in width than the wider portion and a substrate for holding the ground conductor layer, the substrate being located under the ground conductor layer composed of a dielectric material, wherein the dielectric layer has a dielectric constant higher than a dielectric constant of the substrate,

wherein the dielectric layer contains a titanium oxide.

4. (Currently amended) The microstrip line of claim 3, A microstrip line comprising:

a ground conductor layer;

a dielectric layer disposed on the ground conductor layer;

a linear conductor layer disposed on the dielectric layer to have a linear configuration,

the linear conductor layer having a wider portion in an upper part of a cross section thereof taken in a direction perpendicular to a direction in which the linear conductor layer extends and a narrower portion in a lower part of the cross section, the narrower portion being smaller in width than the wider portion and a substrate for holding the ground conductor layer, the substrate being located under the ground conductor layer composed of a dielectric material, wherein the dielectric layer has a dielectric constant higher than a dielectric constant of the substrate, wherein the dielectric layer contains a titanium oxide, and

wherein the titanium oxide is a strontium titanate.

5. (Withdrawn) A method for fabricating a microstrip line, the method comprising the steps of:

forming a ground conductor layer on a substrate composed of a dielectric material;

forming a dielectric layer on the ground conductor layer;

forming a mask pattern having a linear opening on the dielectric layer;

depositing a layer forming a linear conductor layer on the mask pattern including the opening; and

patterning the linear-conductor-layer forming layer such that the linear-conductor-layer, a dielectric layer forming layer on the mask patter has a width larger than a width of the opening.

6. (Withdrawn) An inductor element comprising a microstrip line composed of a ground conductor layer, a dielectric layer formed on the ground conductor layer, and a linear conductor layer formed on the dielectric layer to have a linear configuration,

the linear conductor layer being formed in a spiral configuration in a plane parallel to the dielectric layer and having a wider portion in an upper part of a cross section thereof taken in a direction perpendicular to a direction in which the linear conductor layer extends and a narrower portion in a lower part of the cross section, the narrower portion being smaller in width than the wider portion.

7. (Withdrawn) An RF semiconductor device comprising:
an active element formed in a substrate; and
a microstrip line formed on the substrate to propagate input/output signals to and from the active element,

the microstrip line being composed of a ground conductor layer formed on the substrate, and a dielectric layer formed on the dielectric layer to have a linear configuration,

the linear conductor layer having a wider portion in an upper part of a cross section thereof taken in a direction perpendicular to a direction in which the linear conductor layer extends and a narrower portion in a lower part of the cross section, the narrower portion being smaller in width than the wider portion.